

EAST Search History**EAST Search History (Prior Art)**

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L4	11375	((clean\$4 reclaim\$4 recover\$4 reus\$4 re-us\$4) with (silicon si wafer semiconductor substrate work adj piece workpiece chip)) same (copper cu)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/18 16:24
L2	5666	((134/1) or (134/1.3) or (216/55) or (216/87) or (216/96) or (216/99)).CCLS.	US_PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/18 16:24
L5	266	2 and 4	US_PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/18 16:25
L7	111	reclaim\$3 with wafer and (copper cu)	US_PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/18 16:28
L10	674918	(156/345.\$).CCLS. or ((134") or ("216") or ("438") or ("451") or ("432") or ("205") or ("250")).CLAS.	US_PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/18 16:30
L13	4390	((decontaminat\$3 contaminat\$4 reclaim \$4 recover\$4 reus\$4 re-us\$4) with (silicon si wafer semiconductor substrate work adj piece workpiece chip)) same (copper cu) and (etch\$4 remov\$4 clean \$4) and (heat\$4 anneal \$4 thermal\$4 bak\$4)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/18 16:32
L14	1911	10 and 13	US_PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/18 16:33

L15	5543	((decontaminat\$3 contamina\$4 reclaim \$4 recover\$4 reus\$4 re-us\$4) with (silicon si wafer semiconductor substrate work adj piece workpiece chip)) and (etch\$4 remov\$4 clean\$4) and (heat\$4 anneal\$4 thermal\$4 bak\$4) and (remov\$4 diffus\$4 outdiffus\$4 getter\$4) with (copper cu)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/18 16:34
L16	1	10/ 677309	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/18 16:37
L18	67	(sc1 sc-1 sc2 sc-2 standard adj clean\$3 rca near2 clean\$3 (hydrogen adj peroxide "h.sub.2o. sub.2") with (hydrochloric hcl ammonium adj hydroxide "nh. sub.4oh") same (copper cu) same (diffus\$4 extract\$4 outdiffus\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/18 16:43
L17	5714	((decontaminat\$3 contamina\$4 reclaim \$4 recover\$4 reus\$4 re-us\$4) with (silicon si wafer semiconductor substrate work adj piece workpiece chip)) and (etch\$4 remov\$4 clean\$4) and (heat\$4 anneal\$4 thermal\$4 bak\$4) and (remov\$4 diffus\$4 outdiffus\$4 getter\$4 extract\$4) with (copper cu)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/18 16:43
L22	60	20 not 21	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/18 16:44

L21	138	20 and 10	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/18 16:44
L20	198	17 and 19	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/18 16:44
L19	1416	(sc1 sc-1 sc2 sc-2 standard adj clean\$3 rca near2 clean\$3 (hydrogen adj peroxide "h.sub.2o. sub.2") with (hydrochloric hcl ammonium adj hydroxide "nh. sub.4oh") same (copper cu)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/18 16:44
L23	1	(sc1 sc-1 sc2 sc-2 standard adj clean\$3 rca near2 clean\$3 (hydrogen adj peroxide "h.sub.2o. sub.2") near5 (hydrochloric hcl ammonium adj hydroxide "nh. sub.4oh") near10 (copper cu) and ((decontaminat\$3 contamina\$4 reclaim \$4 recover\$4 reus\$4 re-us\$4) near5 (silicon si wafer semiconductor substrate work adj piece workpiece chip)) and (etch\$4 remov\$4 clean\$4) and (heat\$4 anneal\$4 thermal\$4 bak\$4) and (remov\$4 diffus\$4 outdiffus\$4 getter\$4 extract\$4) near5 (copper cu)	USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/18 16:45

L24	2	(sc1 sc-1 sc2 sc-2 standard adj clean\$3 rca near2 clean\$3 (hydrogen adj peroxide "h.sub.2o. sub.2") near5 (hydrochloric hcl ammonium adj hydroxide "nh. sub.4oh") and ((decontaminat\$3 contamina\$4 reclaim \$4 recover\$4 reus\$4 re-us\$4) near5 (silicon si wafer semiconductor substrate work adj piece workpiece chip)) and (etch\$4 remov\$4 clean\$4) and (heat\$4 anneal\$4 thermal\$4 bak\$4) and (remov\$4 diffus\$4 outdiffus\$4 getter\$4 extract\$4) near5 (copper cu)	USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/18 16:46
L25	7	(sc1 sc-1 sc2 sc-2 standard adj clean\$3 rca near2 clean\$3 (hydrogen adj peroxide "h.sub.2o. sub.2") near5 (hydrochloric hcl ammonium adj hydroxide "nh. sub.4oh") and ((decontaminat\$3 contamina\$4 reclaim \$4 recover\$4 reus\$4 re-us\$4) near5 (silicon si wafer semiconductor substrate work adj piece workpiece chip)) and (etch\$4 remov\$4 clean\$4) and (heat\$4 anneal\$4 thermal\$4 bak\$4) and (remov\$4 diffus\$4 outdiffus\$4 getter\$4 extract\$4) and (copper cu)	USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/18 16:47

L26	35	(sc1 sc-1 sc2 sc-2 standard adj clean\$3 rca near2 clean\$3 (hydrogen adj peroxide "h.sub.2o. sub.2") near5 (hydrochloric hcl ammonium adj hydroxide "nh. sub.4oh") and ((decontaminat\$3 contamina\$4 reclaim \$4 recover\$4 reus\$4 re-us\$4) and (silicon si wafer semiconductor substrate work adj piece workpiece chip)) and (etch\$4 remov\$4 clean\$4) and (heat\$4 anneal\$4 thermal\$4 bak\$4) and (remov\$4 diffus\$4 outdiffus\$4 getter\$4 extract\$4) and (copper cu)	USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/18 16:49
L27	28	26 not 25	USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/18 16:50
L28	594	5 7 18 20	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/18 16:55
L29	171	(216/55).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/18 17:04
L31	92	30 not 28	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/18 17:05
L30	96	29 and (silicon si wafer semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/18 17:05

L33	12	("4144099" "4231809" "4732874" "4878988" "4994399" "5272119" "6008140" "6012970" "6020639" "6022265").PN. OR ("6100167").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/18 17:50
L36	42	("3559281" "3905162" "3923567" "4276114" "4663890" "4892612" "5409770" "5538465").PN. OR ("5622875").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/18 17:52
L39	58	("3556879" "3559281" "3701696" "3811975" "3869313").PN. OR ("3923567").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/18 17:54
L38	10	("3923567" "5622875" "5855735" "5885334" "6384415" "6406923" "6451696").PN. OR ("6884634").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/18 17:54
L40	18	("5238500" "5486266" "5516730" "5681397" "5681398").PN. OR ("5932022").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/18 17:55
L41	7	("5272119" "5294570" "5489557" "5509970" "5681397" "5714203" "5814157").PN. OR ("6482269").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/18 17:57

L42	29	("4724171" "4863561" "4885056" "4973563" "5051134" "5181985" "5219613" "5275667" "5288333" "5290361" "5308400").PN. OR ("5516730").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/18 17:58
L45	40	44 and (silicon si wafer semiconductor) and (copper cu)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/18 17:59
L44	123	43 not 28 not 30	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/18 17:59
L43	145	33 36 38 39 40 41 42	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/18 17:59
L46	9	("3923567" "5100501" "5426061" "5840590").PN. OR ("6054373").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/18 18:03

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